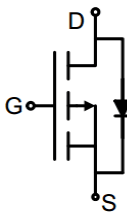
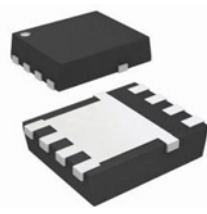


## P-Channel Trench MOSFET

<b>Description</b> <p>The G16P03D3 uses advanced trench technology to provide excellent <math>R_{DS(ON)}</math>, low gate charge. It can be used in a wide variety of applications.</p>		 Schematic diagram	
<b>General Features</b> <ul style="list-style-type: none"> <li>● <math>V_{DS}</math> -30V</li> <li>● <math>I_D</math> (at <math>V_{GS} = -10V</math>) -16A</li> <li>● <math>R_{DS(ON)}</math> (at <math>V_{GS} = -10V</math>) &lt; 12m<math>\Omega</math></li> <li>● <math>R_{DS(ON)}</math> (at <math>V_{GS} = -4.5V</math>) &lt; 18m<math>\Omega</math></li> <li>● 100% Avalanche Tested</li> <li>● RoHS Compliant</li> </ul>		 DFN3X3-8L	
<b>Application</b> <ul style="list-style-type: none"> <li>● Power switch</li> <li>● DC/DC converters</li> </ul>			
<b>Device</b>	<b>Package</b>	<b>Marking</b>	<b>Packaging</b>
G16P03D3	DFN3X3-8L	G16P03	4000pcs/Reel

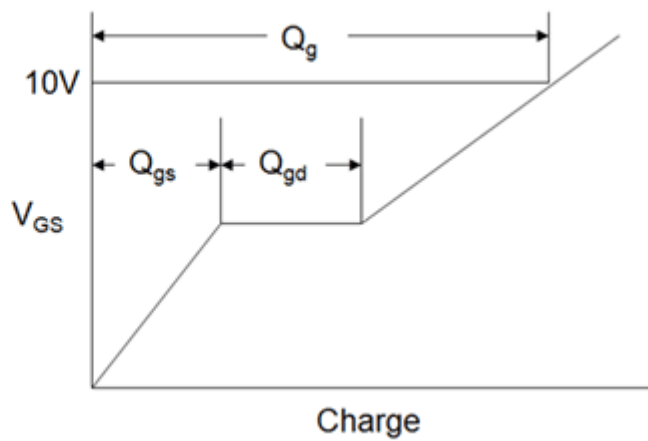
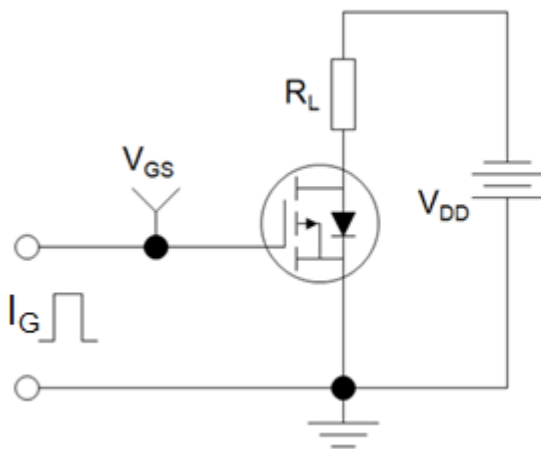
<b>Absolute Maximum Ratings</b> $T_C = 25^\circ\text{C}$ , unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Continuous Drain Current	$I_D$	-16	A
Pulsed Drain Current (note1)	$I_{DM}$	-64	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation	$P_D$	3	W
Single Pulse Avalanche Energy (note3)	$E_{as}$	116	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 To 150	$^\circ\text{C}$
<b>Thermal Resistance</b>			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	41	$^\circ\text{C/W}$

Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static Parameters</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$	--	--	-1	$\mu A$
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -10A$	--	8.5	12	m $\Omega$
		$V_{GS} = -4.5V, I_D = -7A$	--	12	18	
Forward Transconductance	$g_{FS}$	$V_{DS} = -15V, I_D = -3A$	--	42	--	S
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = -15V,$ $f = 1.0\text{MHz}$	--	1995	--	pF
Output Capacitance	$C_{oss}$		--	300	--	
Reverse Transfer Capacitance	$C_{rss}$		--	260	--	
Total Gate Charge	$Q_g$	$V_{DD} = -15V,$ $I_D = -10A,$ $V_{GS} = -10V$	--	35	--	nC
Gate-Source Charge	$Q_{gs}$		--	5.7	--	
Gate-Drain Charge	$Q_{gd}$		--	8.8	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15V,$ $I_D = -10A,$ $R_G = 1\Omega$	--	11	--	ns
Turn-on Rise Time	$t_r$		--	7.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	43.5	--	
Turn-off Fall Time	$t_f$		--	17.5	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	-16	A
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = -10A, V_{GS} = 0V$	--	--	-1.2	V
Reverse Recovery Time	$T_{rr}$	$I_S = 10A, V_{GS} = 0V$ $di/dt = 500A/\mu s$	--	13.3	--	ns

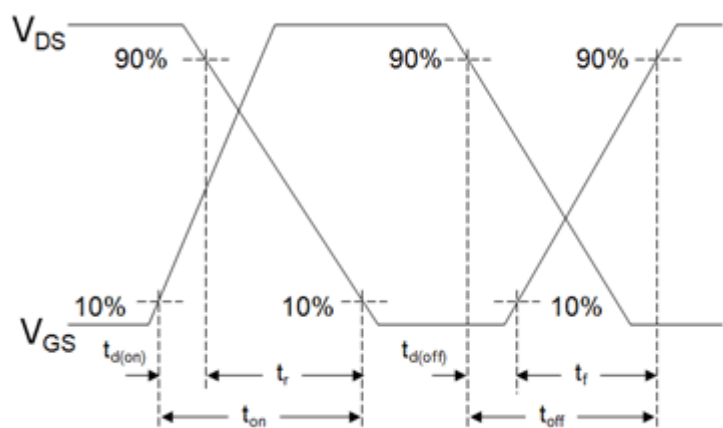
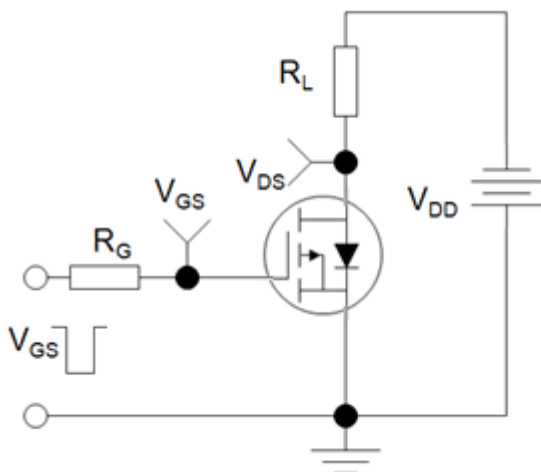
**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical  $R_G$
3.  $V_{DD} = 50V, R_G = 25\Omega, L = 0.5\text{ mH}$ , Starting  $T_J = 25^\circ\text{C}$  .

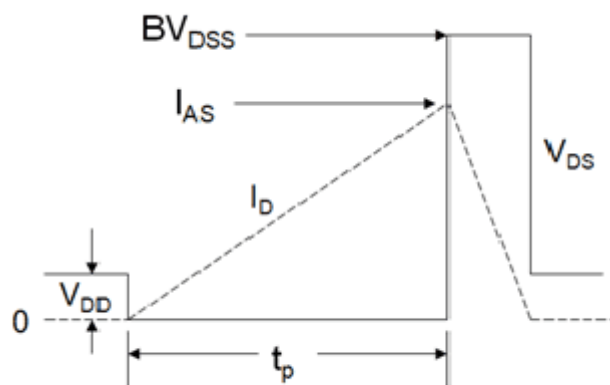
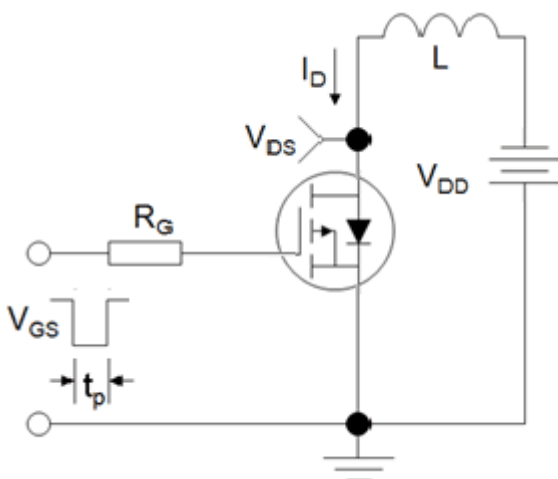
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

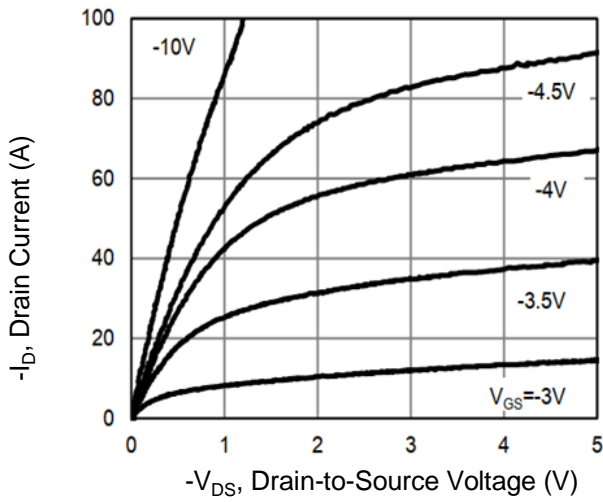


Figure 2. Transfer Characteristics

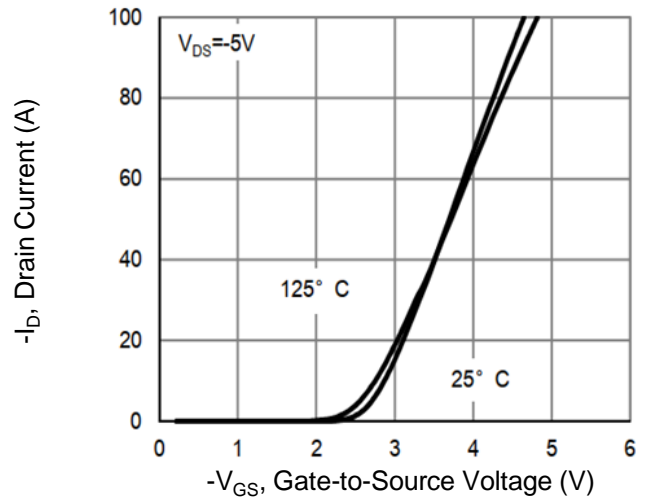


Figure 3.  $R_{DS(on)}$  vs  $V_{GS}$

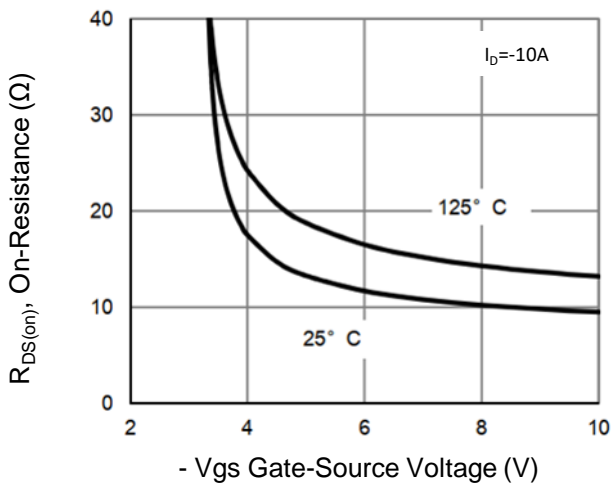


Figure 4. Gate Charge

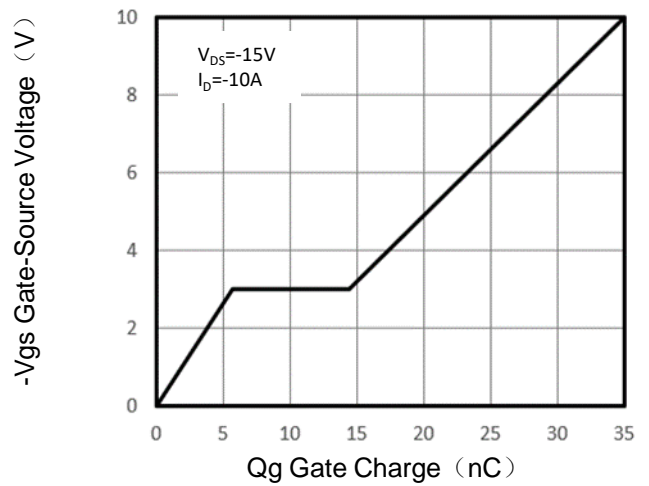


Figure 5. Capacitance vs  $V_{DS}$

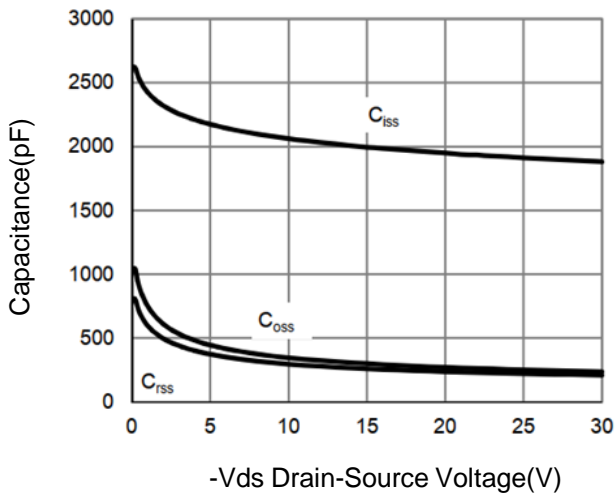
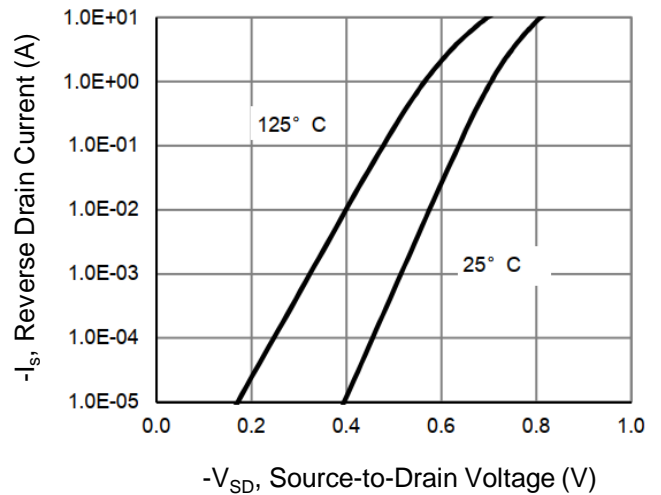


Figure 6. Source-Drain Diode Forward



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. Drain-Source On-Resistance

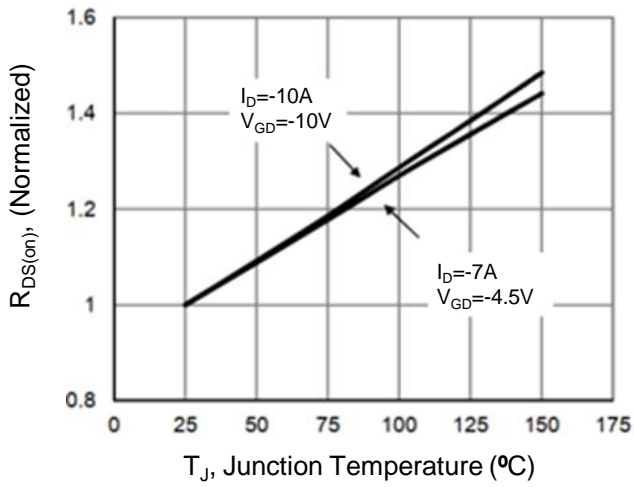


Figure 10. Safe Operation Area

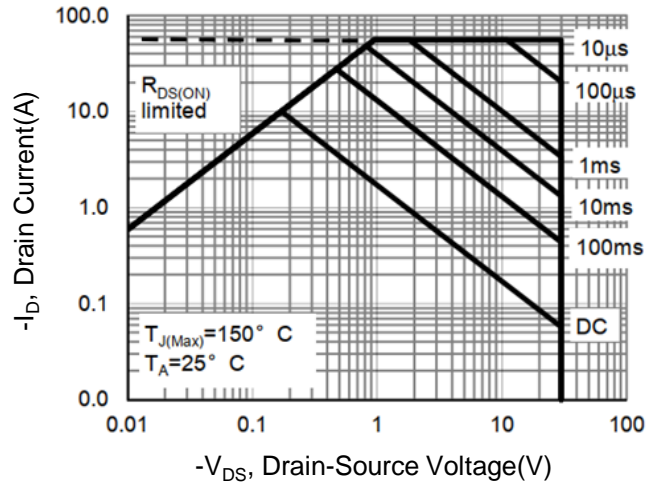
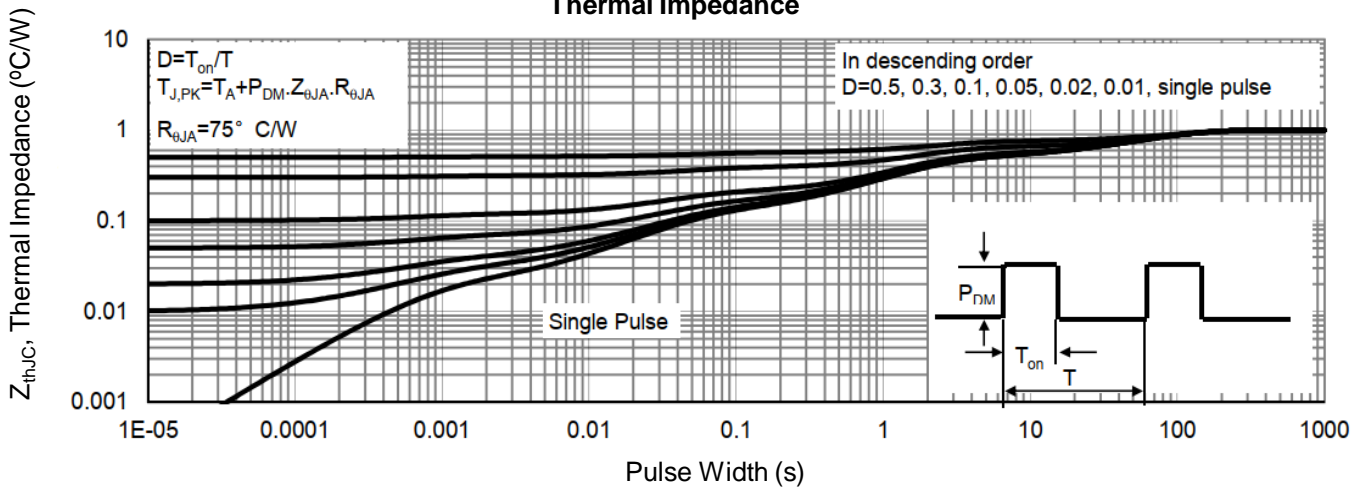
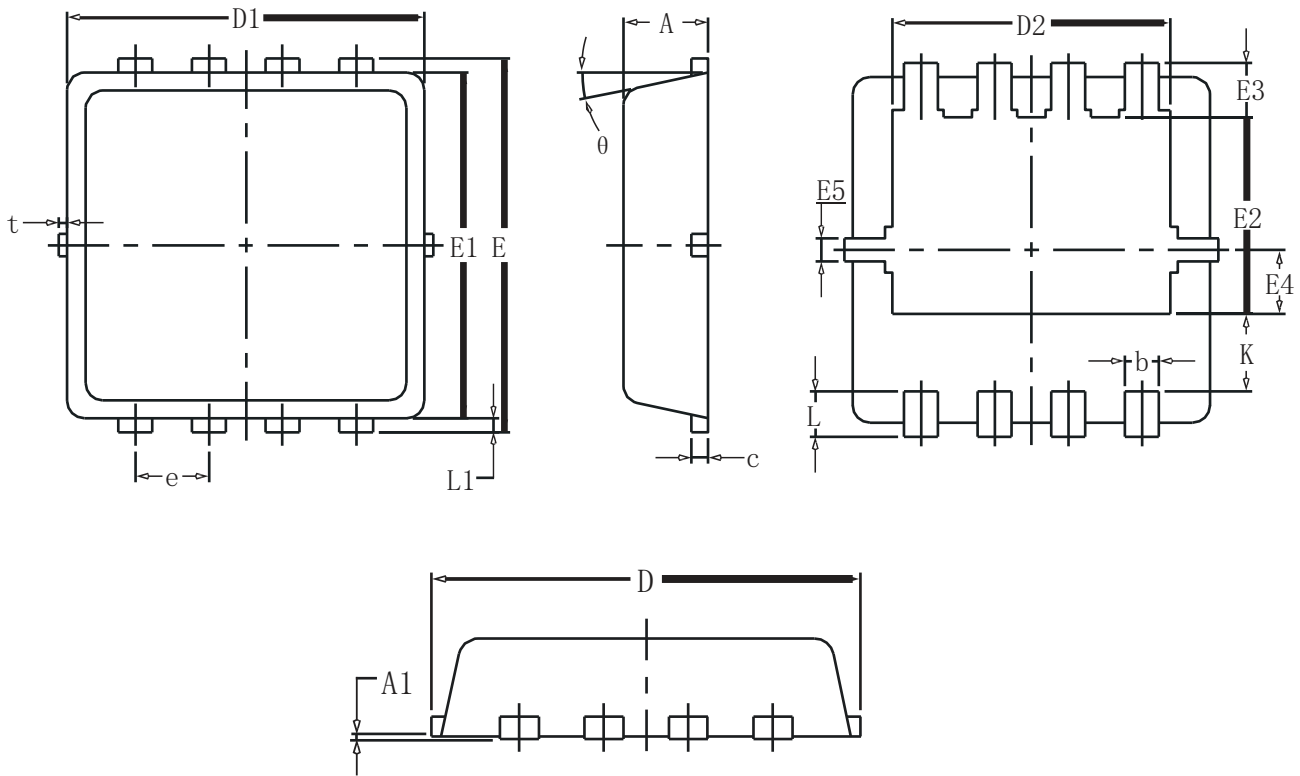


Figure 9. Normalized Maximum Transient Thermal Impedance



DFN3X3-8L Package information



SYMBOL	COMMON		
	MM		
	MIN	NOM	MAX
A	0.70	0.75	0.85
A1	-	-	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
θ	10°	12°	14°